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H. Hamada, *Kinki Univ., Japan*

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13:50 (6-3)	Unseeded Growth of Poly-Crystalline Ge with (111) Surface Orientation on Insulator by Pulsed Green Laser Annealing M. Horita <sup>1</sup> , T. Takao <sup>1</sup> , Y. Nieda <sup>1</sup> , Y. Ishikawa <sup>1</sup> , N. Sasaki <sup>2</sup> , Y. Uraoka <sup>1</sup> , <sup>1</sup> <i>Nara Inst. of Sci. and Technol., Japan</i> , <sup>2</sup> <i>Japan Women's Univ., Japan</i> .....	237

— Coffee Break —

**Session 7 : Oxide and LTPS TFTs (14 : 30 ~ 15 : 55)**

<b>Chairpersons :</b>	H. J. Kim, <i>Yonsei Univ., Korea</i> T. Noguchi, <i>Univ. of the Ryukyus, Japan</i>	
14:30 (7-1)	Prospects of Oxide TFTs Approaching LTPS (Invited) K. -S. Park, S. Oh, P. Yun, J. U. Bae, I. B. Kang, <i>LG Display, Korea</i> .....	241
14:55 (7-2)	Suppression of Positive Gate Bias Temperature Stress and Negative Gate Bias Illumination Stress Induced Degradations by Fluorine-Passivated In-Ga-Zn-O Thin-Film Transistors D. Wang <sup>1</sup> , J. Jiang <sup>1,2</sup> , M. Furuta <sup>1</sup> , <sup>1</sup> <i>Kochi Univ. of Technol., Japan</i> , <sup>2</sup> <i>Shenyang Univ. of Technol., China</i> .....	245
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15:35 (7-4)	Controllability of Self-Aligned Four-Terminal Planar Embedded Metal Double-Gate Low- Temperature Polycrystalline-Silicon Thin-Film Transistors on Glass Substrate H. Ohsawa, S. Sasaki, A. Hara, <i>Tohoku Gakuin Univ., Japan</i> .....	253

**Closing Remarks (15 : 55 ~ 16 : 00)**

**Author Interviews (16 : 00 ~ 16 : 30)**